

### FEATURES

- Double Side Cooling
- High Surge Capability

### APPLICATIONS

- High Power Drives
- High Voltage Power Supplies
- Static Switches

### VOLTAGE RATINGS

Part and Ordering Number	Repetitive Peak Voltages $V_{DRM}$ and $V_{RRM}$ V	Conditions
DCR390J85*	8500	$T_{vj} = -40^{\circ}\text{C}$ to $125^{\circ}\text{C}$ , $I_{DRM} = I_{RRM} = 100\text{mA}$ , $V_{DRM}, V_{RRM} t_p = 10\text{ms}$ , $V_{DSM} \& V_{RSM} =$ $V_{DRM} \& V_{RRM} + 100\text{V}$ respectively
DCR390J80	8000	
DCR390J70	7000	

Lower voltage grades available.  
 \*8200V @  $-40^{\circ}\text{C}$ , 8500V @  $0^{\circ}\text{C}$

### ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

### DCR390J85

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

### KEY PARAMETERS

$V_{DRM}$	<b>8500V</b>
$I_{T(AV)}$	<b>387A</b>
$I_{TSM}$	<b>5250A</b>
$dV/dt^*$	<b>1500V/<math>\mu\text{s}</math></b>
$dI/dt$	<b>200A/<math>\mu\text{s}</math></b>

\* Higher  $dV/dt$  selections available

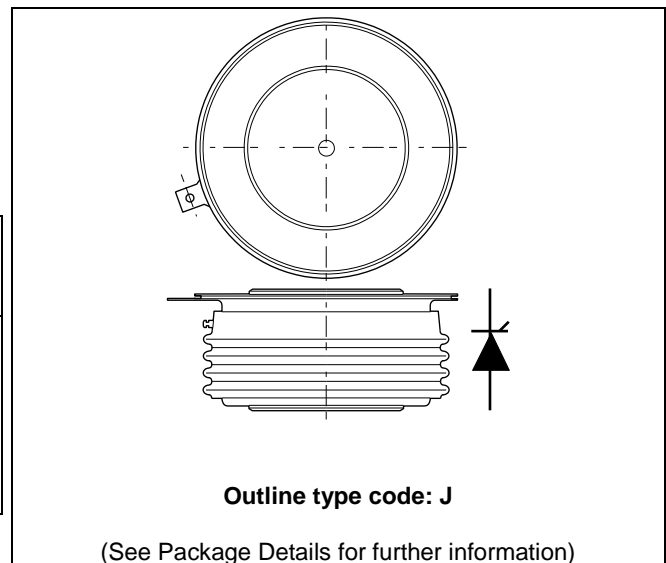


Fig. 1 Package outline

## CURRENT RATINGS

$T_{case} = 60^{\circ}\text{C}$  unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
<b>Double Side Cooled</b>				
$I_{T(AV)}$	Mean on-state current	Half wave resistive load	387	A
$I_{T(RMS)}$	RMS value	-	608	A
$I_T$	Continuous (direct) on-state current	-	583	A

## SURGE RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
$I_{TSM}$	Surge (non-repetitive) on-state current	10ms half sine, $T_{case} = 125^{\circ}\text{C}$	5.25	kA
$I^2t$	$I^2t$ for fusing	$V_R = 0$	0.138	$\text{MA}^2\text{s}$

## THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Conditions	Min.	Max.	Units	
$R_{th(j-c)}$	Thermal resistance – junction to case	Double side cooled	DC	-	0.0379	$^{\circ}\text{C/W}$
		Single side cooled	Anode DC	-	0.0745	$^{\circ}\text{C/W}$
			Cathode DC	-	0.0797	$^{\circ}\text{C/W}$
$R_{th(c-h)}$	Thermal resistance – case to heatsink	Clamping force 11.5kN (with mounting compound)	Double side	-	0.0072	$^{\circ}\text{C/W}$
			Single side	-	.0144	$^{\circ}\text{C/W}$
$T_{vj}$	Virtual junction temperature	Blocking $V_{DRM} / V_{RRM}$	-	125	$^{\circ}\text{C}$	
$T_{stg}$	Storage temperature range		-55	125	$^{\circ}\text{C}$	
$F_m$	Clamping force		10	13	kN	

**DYNAMIC CHARACTERISTICS**

Symbol	Parameter	Test Conditions	Min.	Max.	Units	
$I_{RRM}/I_{DRM}$	Peak reverse and off-state current	At $V_{RRM}/V_{DRM}$ , $T_{case} = 125^{\circ}C$	-	100	mA	
$dV/dt$	Max. linear rate of rise of off-state voltage	To 67% $V_{DRM}$ , $T_j = 125^{\circ}C$ , gate open	-	1500	V/ $\mu s$	
$dI/dt$	Rate of rise of on-state current	From 67% $V_{DRM}$ to $2x I_{T(AV)}$	Repetitive 50Hz	-	100	A/ $\mu s$
		Gate source 30V, 10 $\Omega$ , $t_r < 0.5\mu s$ , $T_j = 125^{\circ}C$	Non-repetitive	-	200	A/ $\mu s$
$V_{T(TO)}$	Threshold voltage – Low level	50A to 400A at $T_{case} = 125^{\circ}C$	-	1.162	V	
	Threshold voltage – High level	400A to 1600A at $T_{case} = 125^{\circ}C$	-	1.3063	V	
$r_T$	On-state slope resistance – Low level	50A to 400A at $T_{case} = 125^{\circ}C$	-	3.153	m $\Omega$	
	On-state slope resistance – High level	400A to 1600A at $T_{case} = 125^{\circ}C$	-	2.763	m $\Omega$	
$t_{gd}$	Delay time	$V_D = 67\% V_{DRM}$ , gate source 30V, 10 $\Omega$ $t_r = 0.5\mu s$ , $T_j = 25^{\circ}C$	-	3	$\mu s$	
$t_q$	Turn-off time	$T_j = 125^{\circ}C$ , $V_R = 100V$ , $dI/dt = 5A/\mu s$ , $dV_{DR}/dt = 20V/\mu s$ linear	-	1200	$\mu s$	
$Q_S$	Stored charge	$I_T = 500A$ , $T_j = 125^{\circ}C$ , $dI/dt = 5A/\mu s$ ,	2000	3000	$\mu C$	
$I_L$	Latching current	$T_j = 25^{\circ}C$ , $V_D = 5V$	-	3	A	
$I_H$	Holding current	$T_j = 25^{\circ}C$ , $R_{G-K} = \infty$ , $I_{TM} = 500A$ , $I_T = 5A$	-	300	mA	

**GATE TRIGGER CHARACTERISTICS AND RATINGS**

Symbol	Parameter	Test Conditions	Max.	Units
V <sub>GT</sub>	Gate trigger voltage	V <sub>DRM</sub> = 5V, T <sub>case</sub> = 25°C	1.5	V
V <sub>GD</sub>	Gate non-trigger voltage	At 50% V <sub>DRM</sub> , T <sub>case</sub> = 125°C	0.4	V
I <sub>GT</sub>	Gate trigger current	V <sub>DRM</sub> = 5V, T <sub>case</sub> = 25°C	350	mA
I <sub>GD</sub>	Gate non-trigger current	At 50% V <sub>DRM</sub> , T <sub>case</sub> = 125°C	15	mA

**CURVES**

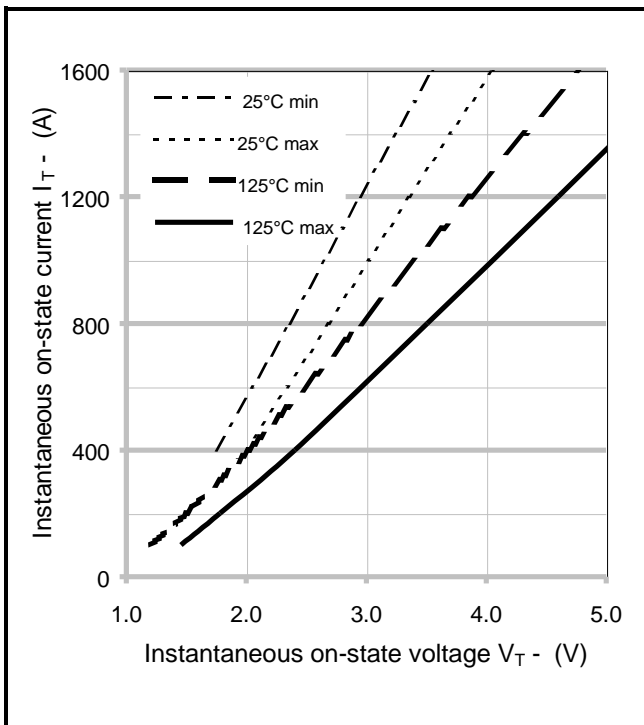


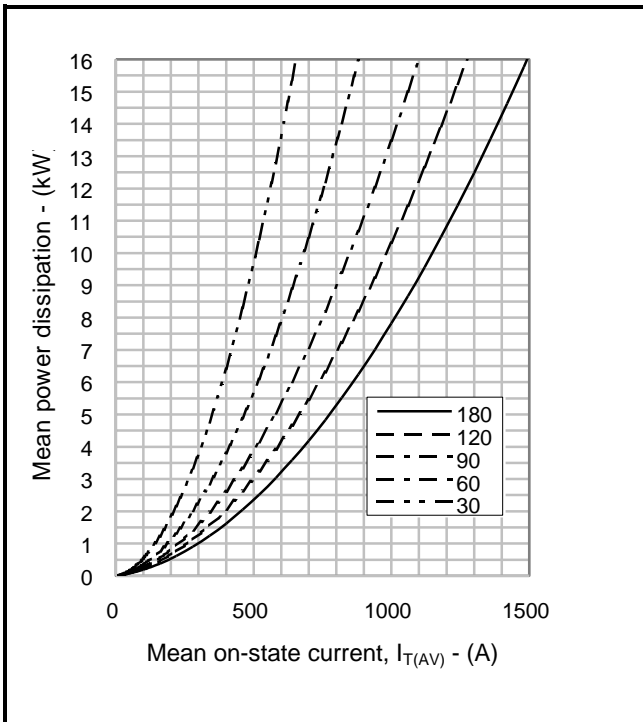
Fig.2 Maximum & minimum on-state characteristics

**V<sub>TM</sub> EQUATION**

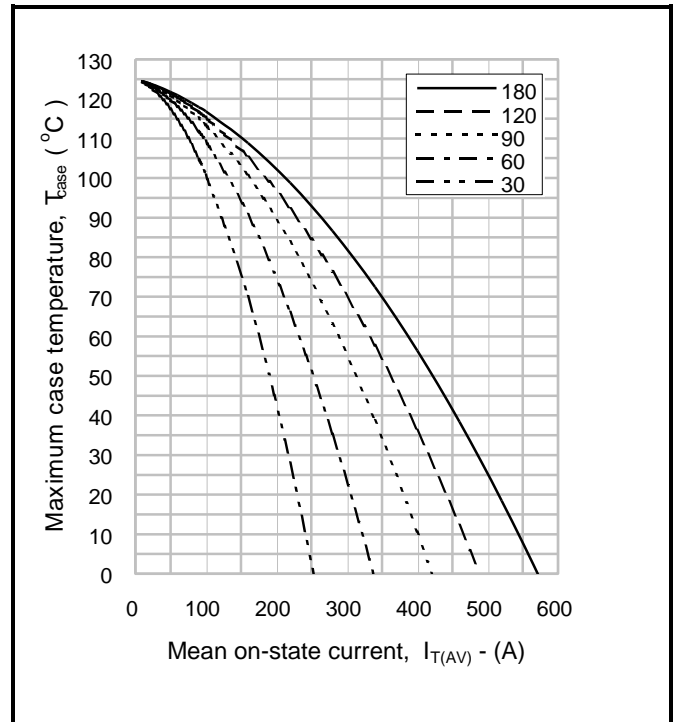
$$V_{TM} = A + B \ln(I_T) + C \cdot I_T + D \cdot \sqrt{I_T}$$

Where A = 1.545561  
 B = -0.202735  
 C = 0.001865  
 D = 0.066158

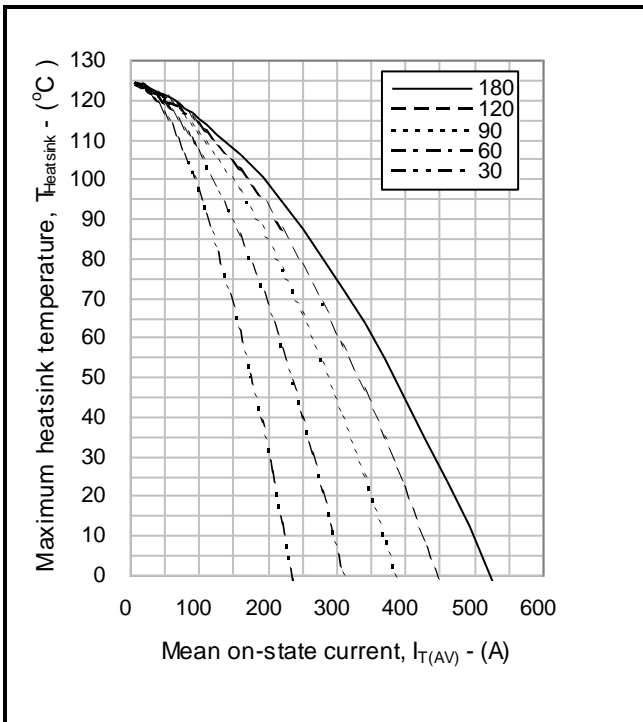
these values are valid for T<sub>j</sub> = 125°C for I<sub>T</sub> 50A to 1600A



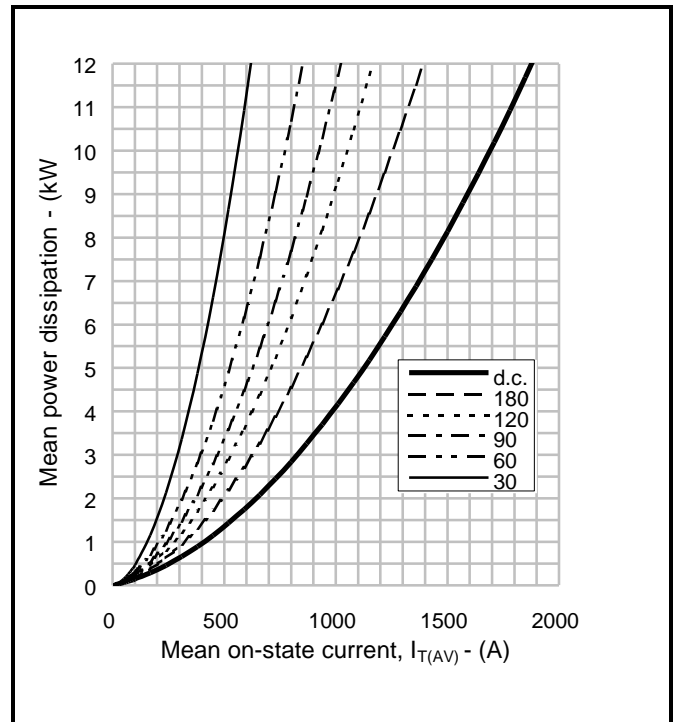
**Fig.3 On-state power dissipation – sine wave**



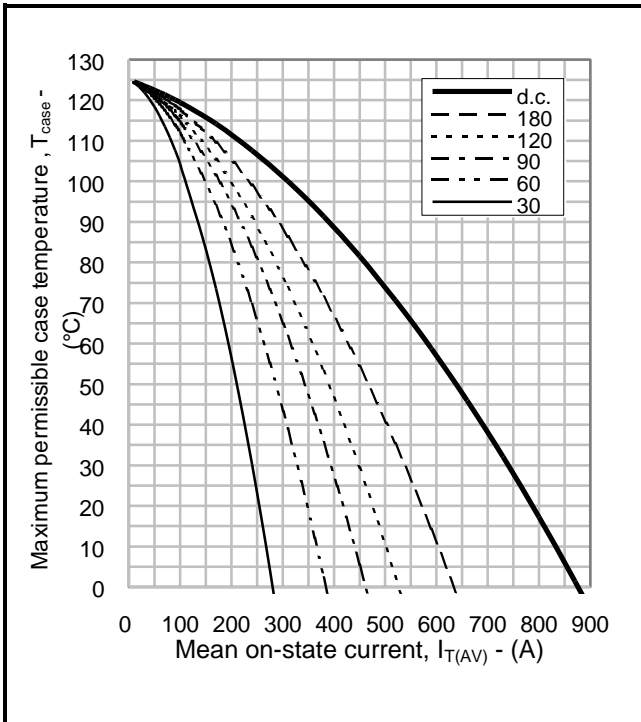
**Fig.4 Maximum permissible case temperature, double side cooled – sine wave**



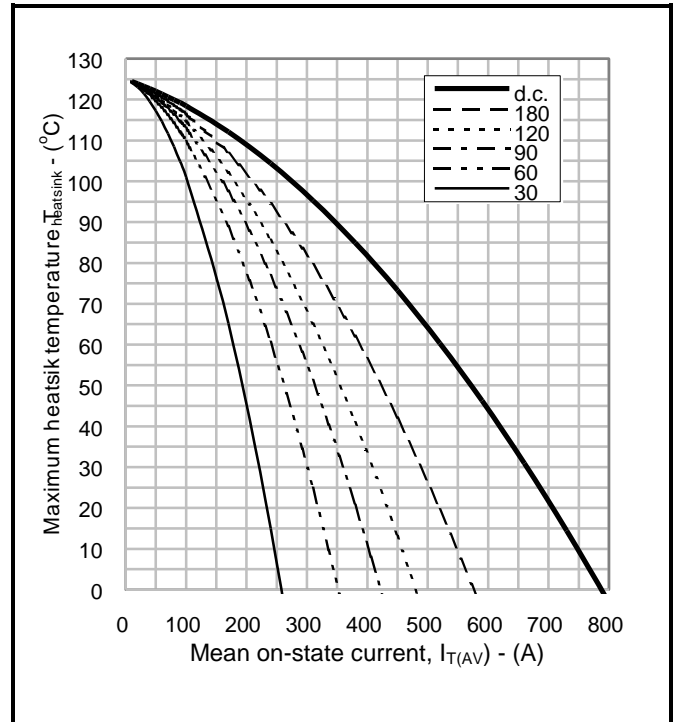
**Fig.5 Maximum permissible heatsink temperature, double side cooled – sine wave**



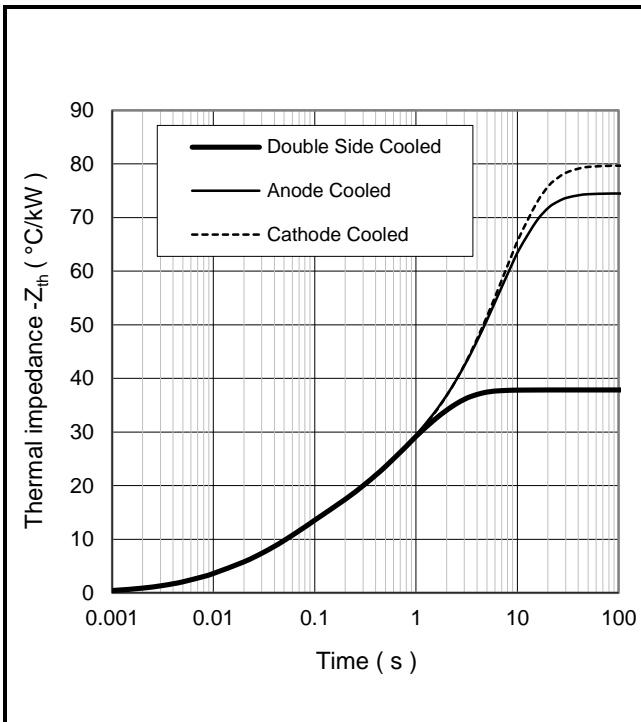
**Fig.6 On-state power dissipation – rectangular wave**



**Fig.7 Maximum permissible case temperature, double side cooled – rectangular wave**



**Fig.8 Maximum permissible heatsink temperature, double side cooled – rectangular wave**



**Fig.9 Maximum (limit) transient thermal impedance – junction to case (°C/kW)**

		1	2	3	4
Double side cooled	R <sub>θj-c</sub> (°C/kW)	2.4256	9.3503	10.6963	15.3758
	T <sub>1</sub> (s)	0.0087759	0.053099	0.4497246	1.395
Anode side cooled	R <sub>θj-c</sub> (°C/kW)	2.8091	9.5576	11.3564	50.6136
	T <sub>1</sub> (s)	0.0097443	0.0591913	0.4759179	6.5548
Cathode side cooled	R <sub>θj-c</sub> (°C/kW)	2.9507	9.4031	11.0771	56.0405
	T <sub>1</sub> (s)	0.0100391	0.0606056	0.4732916	7.228

$$Z_{th} = \sum [R_{\theta} \times (1 - \exp. (-t/t_1))] \quad [1]$$

**ΔR<sub>th(j-c)</sub> Conduction**

Tables show the increments of thermal resistance R<sub>th(j-c)</sub> when the device operates at conduction angles other than d.c.

θ°	Double side cooling	
	sine.	rect.
180	4.43	3.01
120	5.13	4.30
90	5.89	5.03
60	6.58	5.81
30	7.12	6.67
15	7.36	7.13

θ°	Anode Side Cooling	
	sine.	rect.
180	4.39	2.99
120	5.07	4.26
90	5.81	4.97
60	6.48	5.74
30	7.00	6.57
15	7.24	7.01

θ°	Cathode Sided Cooling	
	sine.	rect.
180	4.37	2.98
120	5.05	4.25
90	5.79	4.96
60	6.45	5.72
30	6.97	6.54
15	7.20	6.98

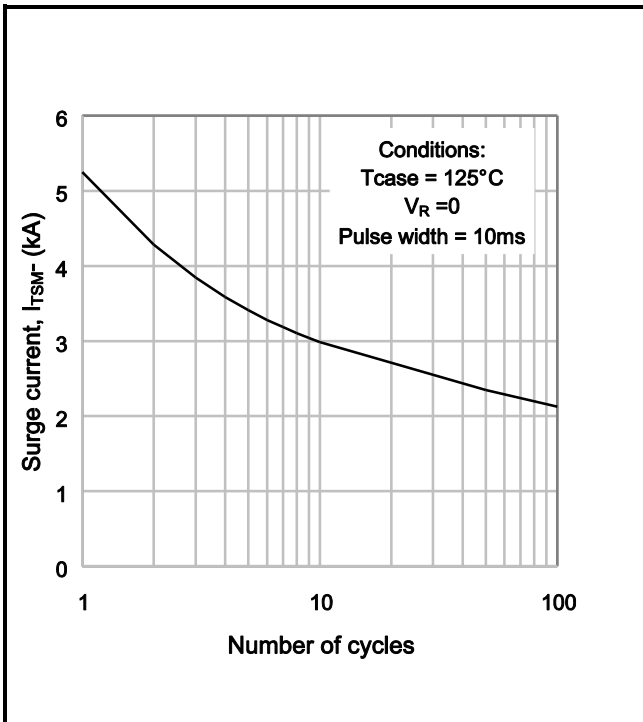


Fig.10 Multi-cycle surge current

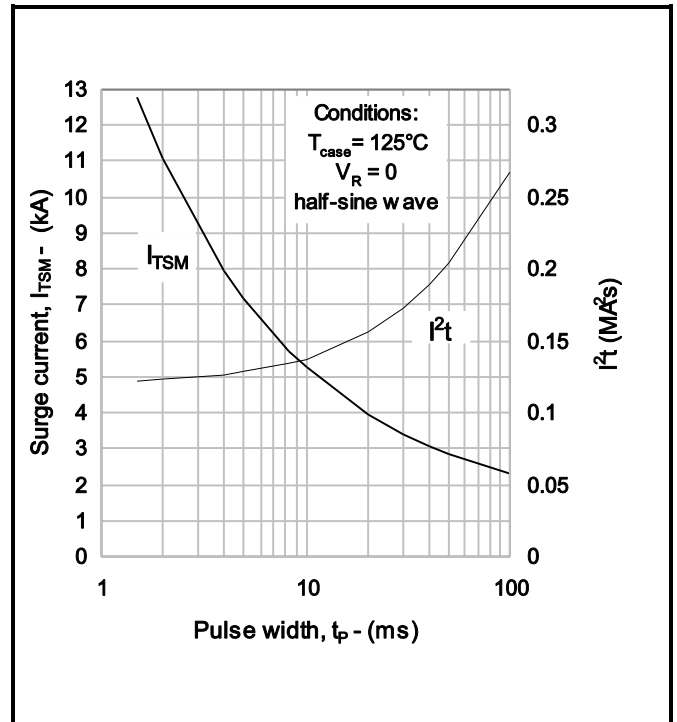


Fig.11 Single-cycle surge current

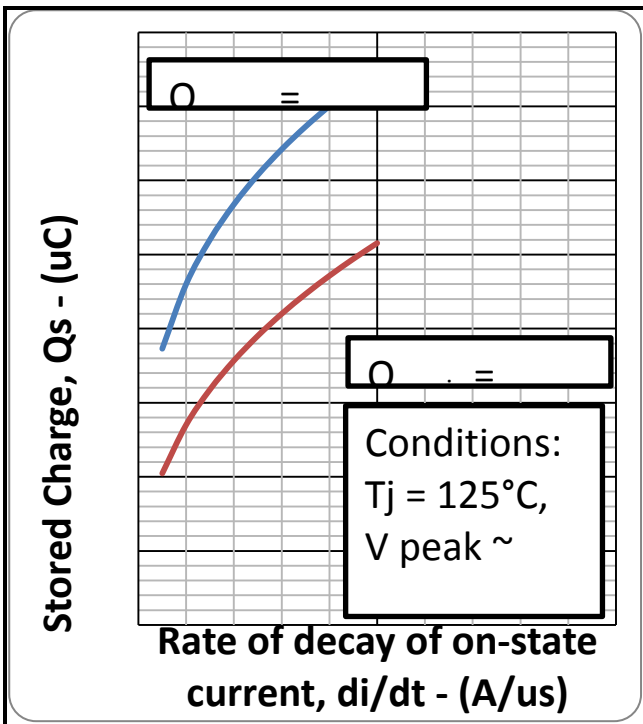


Fig.12 Stored charge

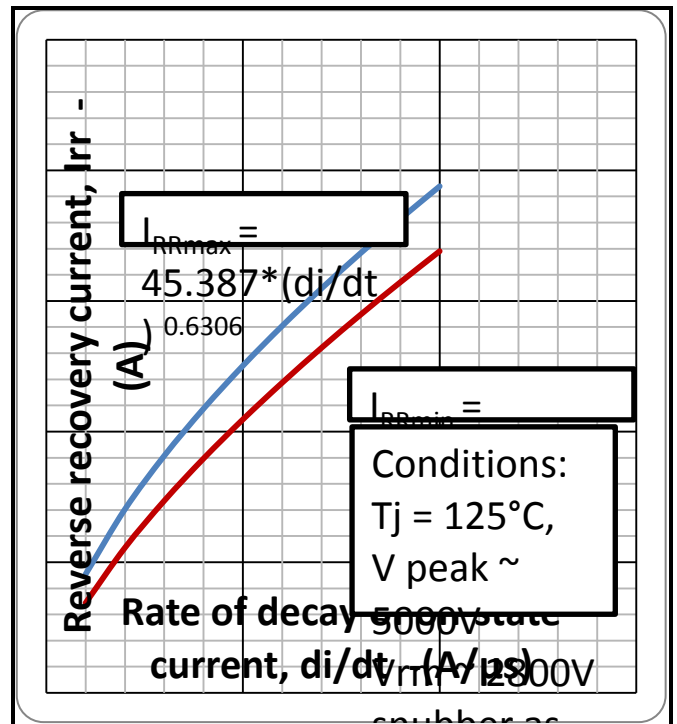


Fig.13 Reverse recovery current

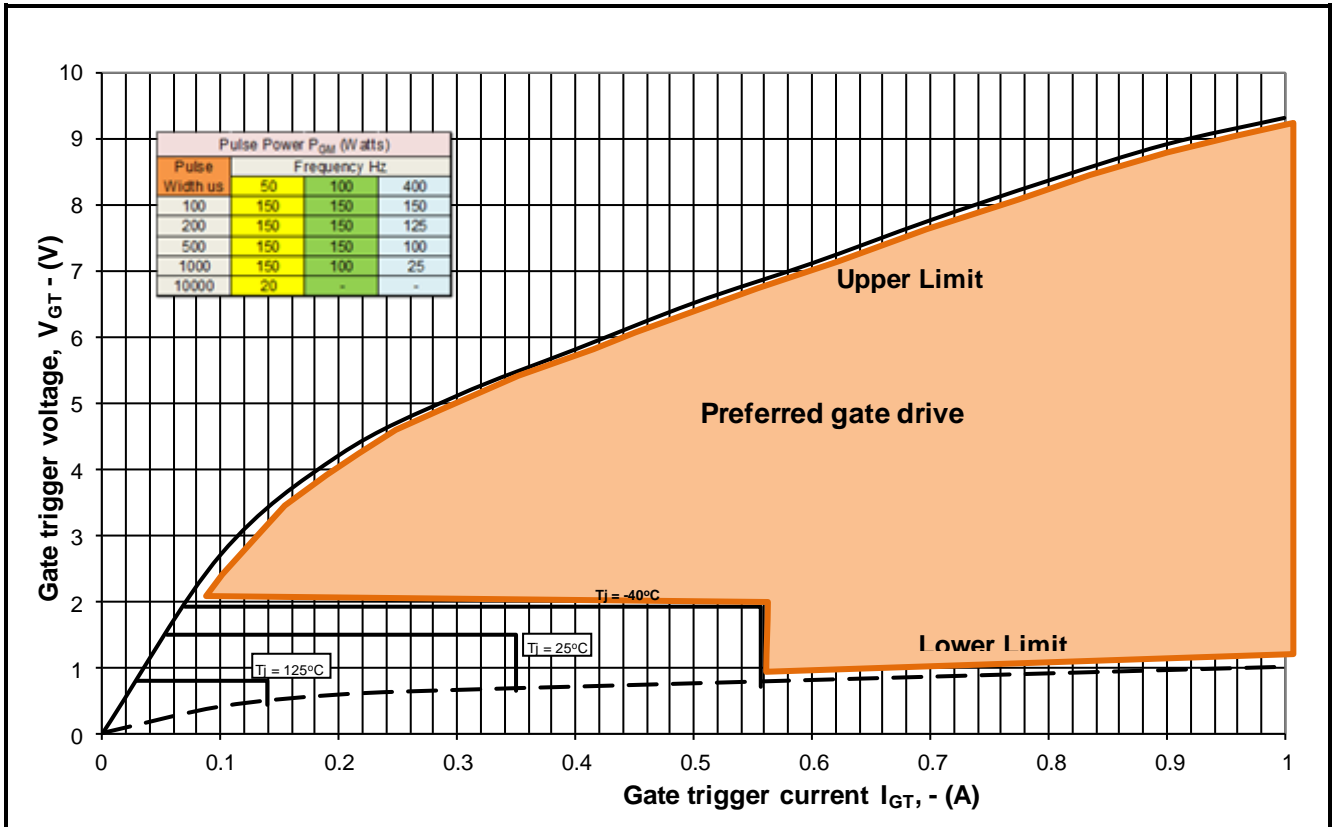


Fig14 Gate Characteristics

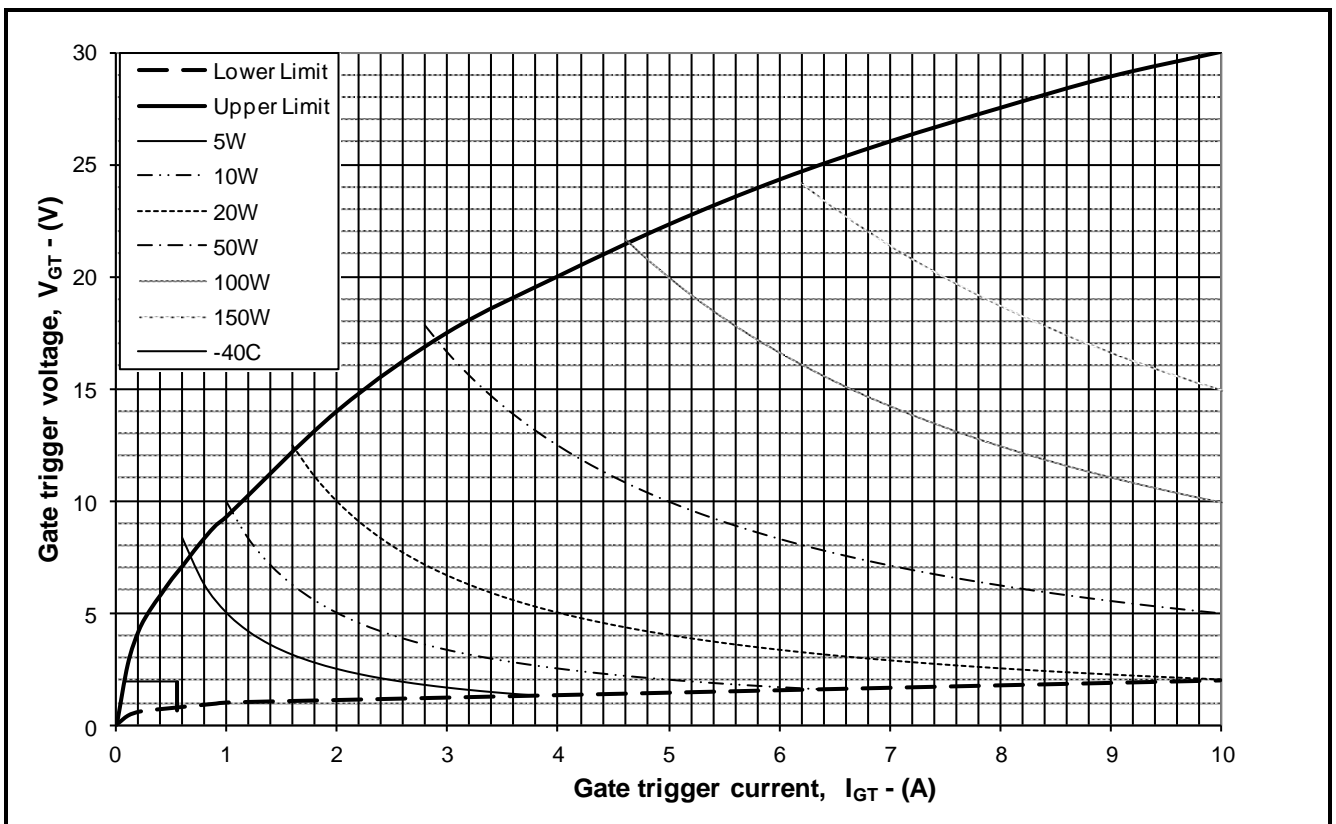
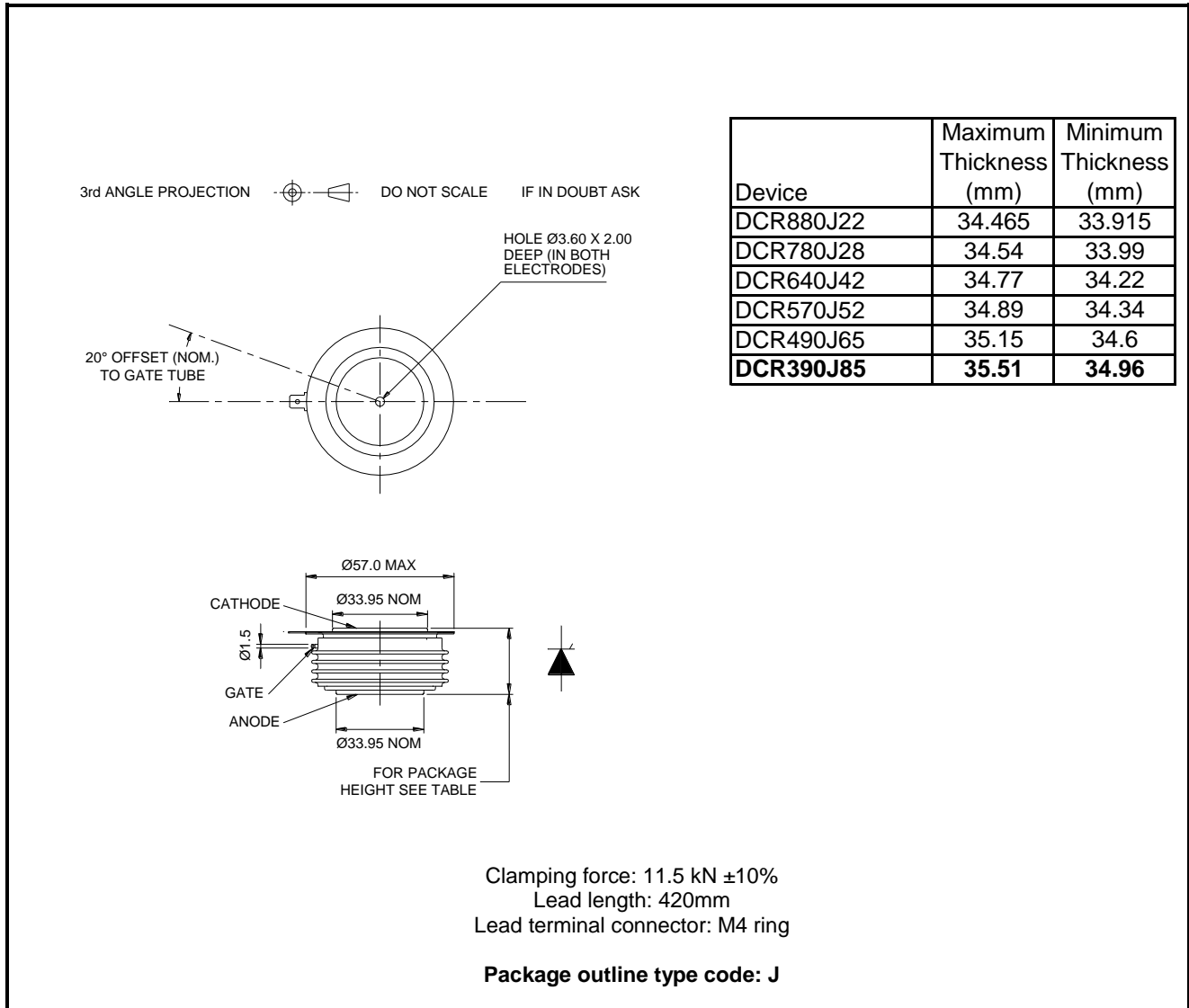


Fig. 15 Gate characteristics



**PACKAGE DETAILS**

For further package information, please contact Customer Services. All dimensions in mm, unless stated otherwise. **DO NOT SCALE.**



**Fig.16 Package outline**

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